

TECHNICAL DATA DATA SHEET 4965, REV. -

HERMETIC POWER MOSFET N-CHANNEL QUAD

FEATURES:

- 100 Volt, 0.18 Ohm, 5A MOSFET
- Fast Switching
- Low R_{DS (on)}
- Characterized at V_{GS} of 6V

MAXIMUM RATINGS

ALL RATINGS ARE AT $\rm T_{\rm C}$ = 25°C UNLESS OTHERWISE SPECIFIED.

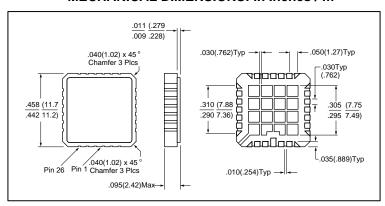
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-		±20	Volts
ON-STATE DRAIN CURRENT	I _D	-	-	5	Amps
PULSED DRAIN CURRENT @ $T_C = 25^{\circ}C$	I _{DM}	•	ı	20	Amps
OPERATING AND STORAGE TEMPERATURE	T _J /T _{STG}	-55		+150	°C
TOTAL DEVICE DISSIPATION @ T _C = 25°C	P_{D}	-	-	27	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	R_{thJC}	-	-	4.7	°C/W

ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV _{DSS}	100	-	-	Volts
$V_{GS} = 0V, I_D = 250\mu A$					
STATIC DRAIN TO SOURCE ON STATE RESISTANCE					
$V_{GS} = 10V, I_D = 3.6A$	R _{DS(ON)}	-	-	0.18	Ω
STATIC DRAIN TO SOURCE ON STATE RESISTANCE					
$V_{GS} = 6V, I_D = 2.4A$	R _{DS(ON)}	-	-	0.20	Ω
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = 250\mu A$	$V_{GS(th)}$	2.0	-	4.0	Volts
FORWARD TRANSCONDUCTANCE	g fs	-	7	-	S(1/Ω)
$V_{DS} = 15V; I_{DS} = 3.6A$					
ZERO GATE VOLTAGE DRAIN CURRENT					
$V_{DS} = 0.8 \text{ x Max. rating}, V_{GS} = 0V$	I _{DSS}	-	-	1	μΑ
$T_{J} = 125^{\circ}C$				100	
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20V$	I _{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20V$				-100	
TURN ON DELAY TIME $V_{DD} = 50V$,	t _{d(ON)}	-	-	30	
RISE TIME $I_D = 3.6A$,	t _r			30	nsec
TURN OFF DELAY TIME $R_G = 6\Omega$	$t_{d(OFF)}$			40	
FALL TIME	t _f			30	
DIODE FORWARD VOLTAGE $I_S = 7.4A, V_{GS} = 0V$	V_{SD}	-	-	1.5	Volts
Pulse test, $t \le 300 \mu s$, duty cycle $d \le 2 \%$					
REVERSE RECOVERY TIME $T_J = 25^{\circ}C$		-	-		
$I_f = 3.6A$	t _{rr}			80	nsec
di/dt ≤ 100A/μsec					
INPUT CAPACITANCE $V_{GS} = 0 V$	C _{iss}	-	370	-	
OUTPUT CAPACITANCE $V_{DS} = 25 \text{ V}$	C _{oss}		60		pF
REVERSE TRANSFER CAPACITANCE f = 1.0MHz	C_{rss}		30		

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MECHANICAL DIMENSIONS: in Inches / m



LCC-28T

PINOUT TABLE

QUAD MOSFET LCC-28T	GATE	DRAIN	SOURCE
MOSFET 1	PIN 1	PINS 5, 6, 7	PINS 2, 3, 4
MOSFET 2	PIN 8	PINS 9, 10, 11	PINS 12, 13, 14
MOSFET 3	PIN 15	PINS 19, 20, 21	PINS 16, 17, 18
MOSFET 4	PIN 22	PINS 23, 24, 25	PINS 26, 27, 28

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